1. A method comprising:

forming a semiconductor substrate having a first exposed polymerizable dielectric surface and a second exposed unpolymerizable surface; and

causing polymerization to occur selectively on the dielectric surface while avoiding polymerization on the unpolymerizable surface to form a polymer that selectively covers the dielectric surface.

2. The method of claim 1 wherein forming a semiconductor substrate includes forming a semiconductor substrate having a second exposed unpolymerizable surface formed of metal.

3. The method of claim 1 wherein forming a semiconductor substrate having an unpolymerizable surface includes forming a copper surface.

4. The method of claim 2 wherein forming a semiconductor substrate having a first exposed dielectric surface includes forming a surface of interlevel dielectric.

5. The method of claim 1 wherein causing polymerization to occur selectively includes surface grafting polymers to the polymerizable surface.

6. The method of claim 1 wherein causing polymerization to occur includes initiating photo induced graft polymerization.

7. The method of claim 6 including coating said substrate with a substance to induce photo surface grafting and polymerization.

8. The method of claim 7 including coating said surface with benzophenone and irradiating using ultraviolet radiation.

9. The method of claim 7 including forming a benzophenone derivative attached to said polymerizable surface through a hydrogen moiety.

10. The method of claim 1 including forming a copper layer over said conductive polymer.

11. A semiconductor structure comprising:

a surface including an exposed polymerizable dielectric and an exposed unpolymerizable region; and

a polymer selectively attached to said polymerizable dielectric to form a surface coating that selectively covers said polymerizable dielectric.

12. The structure of claim 11 wherein said unpolymerizable region is copper.

13. The structure of claim 11 wherein said polymer is a diffusion barrier and a copper layer is formed over said polymer.

14. The structure of claim 11 wherein said polymer is a seed layer and a copper layer is formed over said polymer.

15. The structure of claim 11 wherein said polymer is conductive.

16. The structure of claim 15 wherein said polymer is an oligomer.

17. The structure of claim 16 wherein said polymer is end-functionalized with vinyl groups.

18. The structure of claim 11 wherein said polymer acts as a copper diffusion barrier.

19. The structure of claim 11 wherein said polymer acts as a copper seed layer.

20. The structure of claim 11 wherein said polymer activates electroless deposition of a copper diffusion barrier.

21. The structure of claim 1 wherein said polymer is a monomer including palladium.

22. A method comprising:

forming a semiconductor substrate having a dielectric surface and an exposed metal surface;

causing polymerization to occur selectively on the dielectric surface while avoiding polymerization on the metal surface to form a polymer that selectively covers the dielectric surface; and

using the polymer to form a copper diffusion barrier.

23. The method of claim 21 including forming a monomer that activates electroless deposition of a copper diffusion barrier.

24. A method comprising:

forming a semiconductor substrate having a dielectric surface and a metallic surface;

causing polymerization to occur selectively on the dielectric surface while avoiding polymerization on the

metal surface to form a polymer that selectively covers the dielectric surface; and

forming a copper seed layer using said polymer.

25. The method of claim 24 including forming said polymer using oligomers end-functionalized with vinyl groups.